



# P0130AA

SENSITIVE

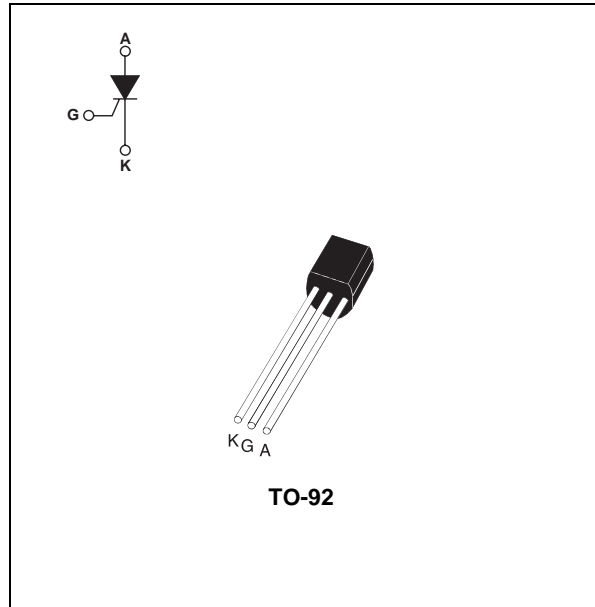
0.8A SCRs

## MAIN FEATURES:

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
$V_{DRM}/V_{RRM}$	100	V
$I_{GT}$	1	$\mu A$

## DESCRIPTION

The P0130AA is a gate sensitive SCR, packaged in TO-92, used in conjunction of a TN22 A.S.D™ and of a resistor in electronic starter for fluorescent tubelamps.



## ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)		$T_I = 55^{\circ}C$	0.8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)		$T_I = 55^{\circ}C$	0.5	A
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	$T_j = 25^{\circ}C$	8	A
		$t_p = 10 \text{ ms}$		7	
$I^2t$	$I^2t$ Value for fusing	$t_p = 10 \text{ ms}$	$T_j = 25^{\circ}C$	0.24	$A^2s$
$di/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^{\circ}C$	50	$A/\mu s$
$I_{GM}$	Peak gate current	$t_p = 20 \mu s$	$T_j = 125^{\circ}C$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^{\circ}C$	0.1	W
$T_{stg}$ $T_j$	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^{\circ}C$

## P0130AA

### ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified)

Symbol	Test Conditions			P0130AA	Unit
I <sub>GT</sub>	V <sub>D</sub> = 12 V    R <sub>L</sub> = 140 Ω	MIN.		0.1	μA
		MAX.		1	
V <sub>GT</sub>		MAX.		0.8	V
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ   R <sub>GK</sub> = 1 kΩ	T <sub>j</sub> = 125°C	MIN.	0.1	V
V <sub>RG</sub>	I <sub>RG</sub> = 10 μA		MIN.	8	V
I <sub>H</sub>	I <sub>T</sub> = 50 mA   R <sub>GK</sub> = 1 kΩ		MAX.	5	mA
I <sub>L</sub>	I <sub>G</sub> = 1 mA   R <sub>GK</sub> = 1 kΩ		MAX.	6	mA
dV/dt	V <sub>D</sub> = 67 % V <sub>DRM</sub> R <sub>GK</sub> = 1 kΩ	T <sub>j</sub> = 125°C	MIN.	25	V/μs
V <sub>TM</sub>	I <sub>TM</sub> = 1.6 A   t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25°C	MAX.	1.95	V
V <sub>t0</sub>	Threshold voltage	T <sub>j</sub> = 125°C	MAX.	0.95	V
R <sub>d</sub>	Dynamic resistance	T <sub>j</sub> = 125°C	MAX.	600	mΩ
I <sub>DRM</sub> I <sub>RDM</sub>	V <sub>DRM</sub> = V <sub>RDM</sub> R <sub>GK</sub> = 1 kΩ	T <sub>j</sub> = 25°C	MAX.	1	μA
		T <sub>j</sub> = 125°C	MAX.	100	

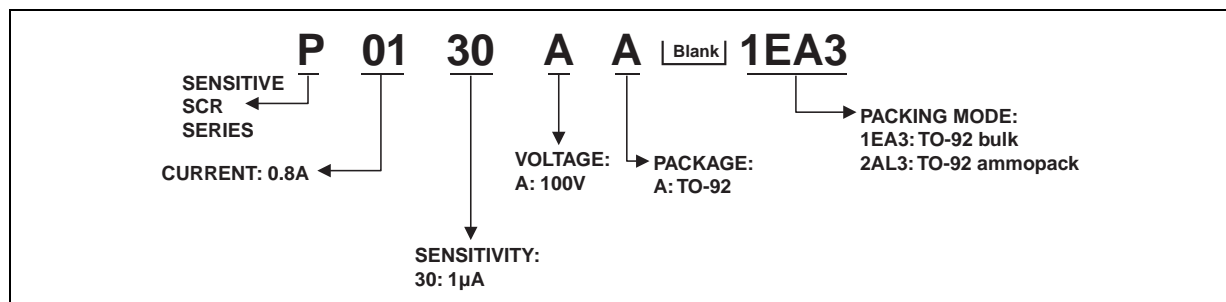
### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-i)</sub>	Junction to case (DC)	80	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	150	°C/W

### PRODUCT SELECTOR

Part Number	Voltage	Sensitivity	Package
P0130AA	100V	1 μA	TO-92

## ORDERING INFORMATION

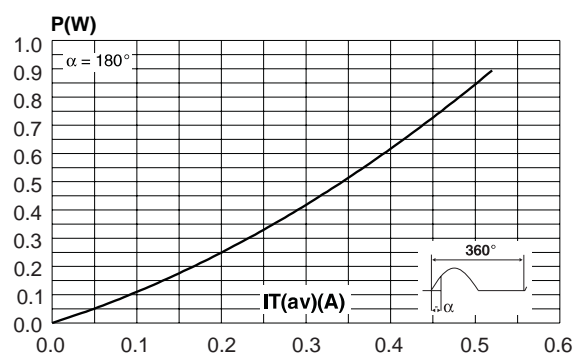


## OTHER INFORMATION

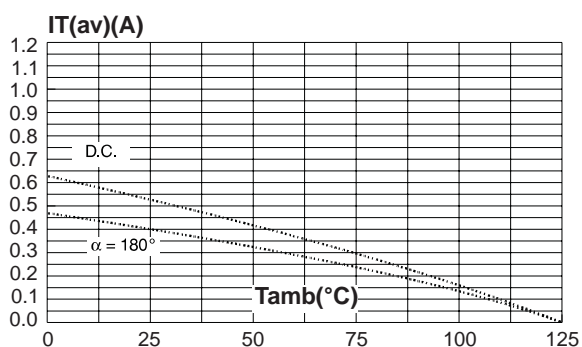
Part Number	Marking	Weight	Base Quantity	Packing mode
P0130AA 1EA3	P0130AA	0.2 g	2500	Bulk
P0130AA 2AL3	P0130AA	0.2 g	2000	Ampack

Note: xx = sensitivity, y = voltage

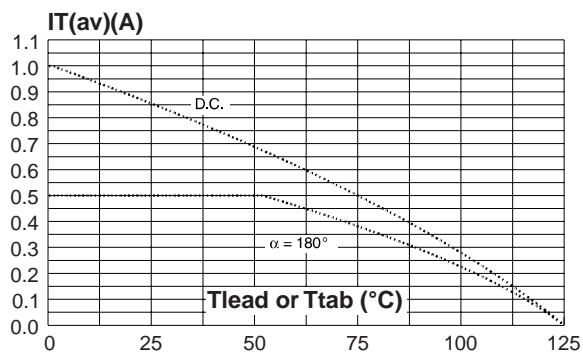
**Fig. 1:** Maximum average power dissipation versus average on-state current.



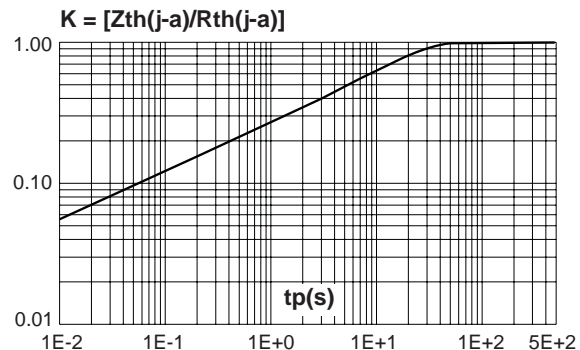
**Fig. 2-2:** Average and D.C. on-state current versus ambient temperature.



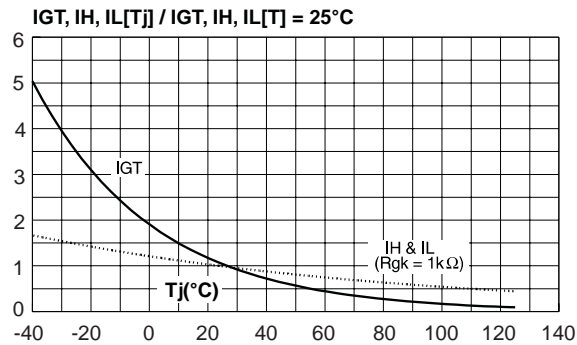
**Fig. 2-1:** Average and D.C. on-state current versus lead temperature.



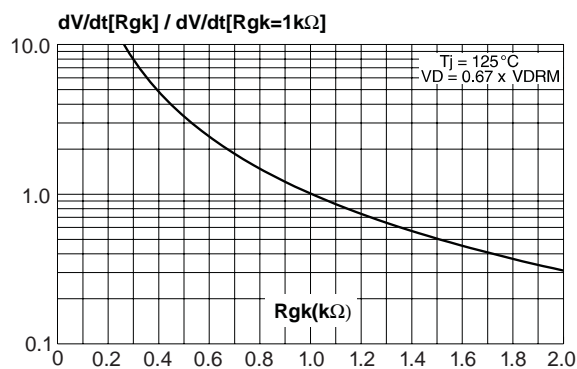
**Fig. 3:** Relative variation of thermal impedance junction to ambient versus pulse duration.



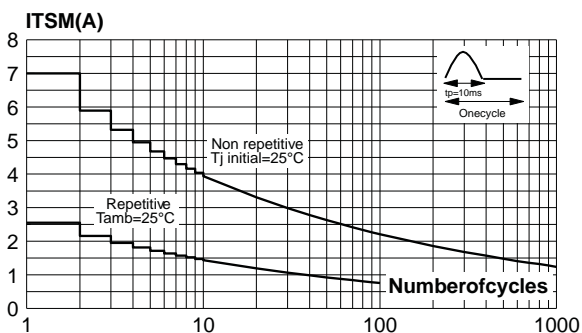
**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



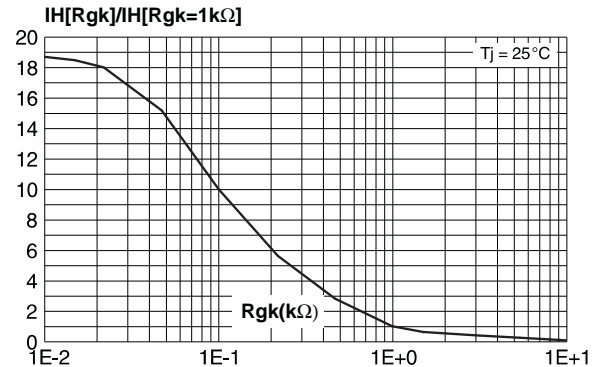
**Fig. 6:** Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).



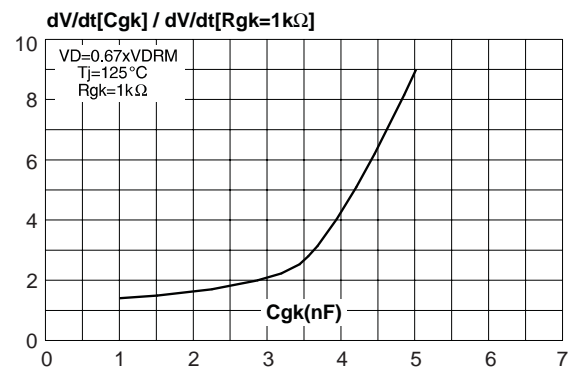
**Fig. 8:** Surge peak on-state current versus number of cycles.



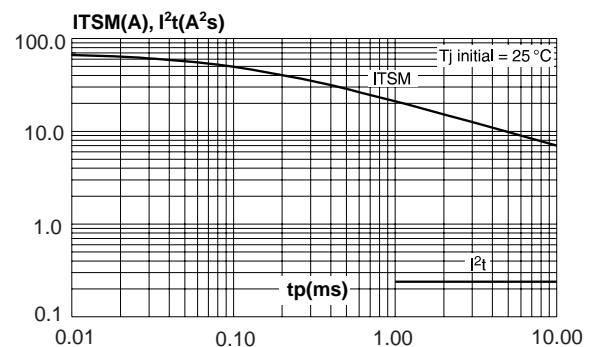
**Fig. 5:** Relative variation of holding current versus gate-cathode resistance (typical values).



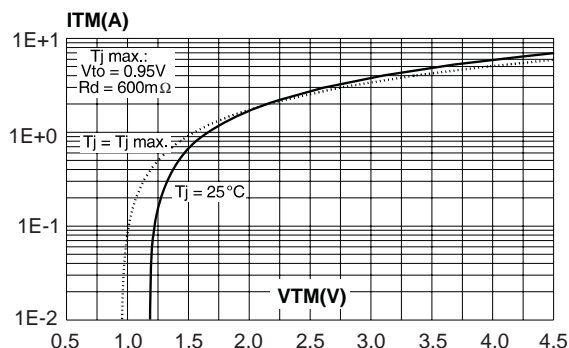
**Fig. 7:** Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values).



**Fig. 9:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ ms}$ , and corresponding value of  $I^2t$ .

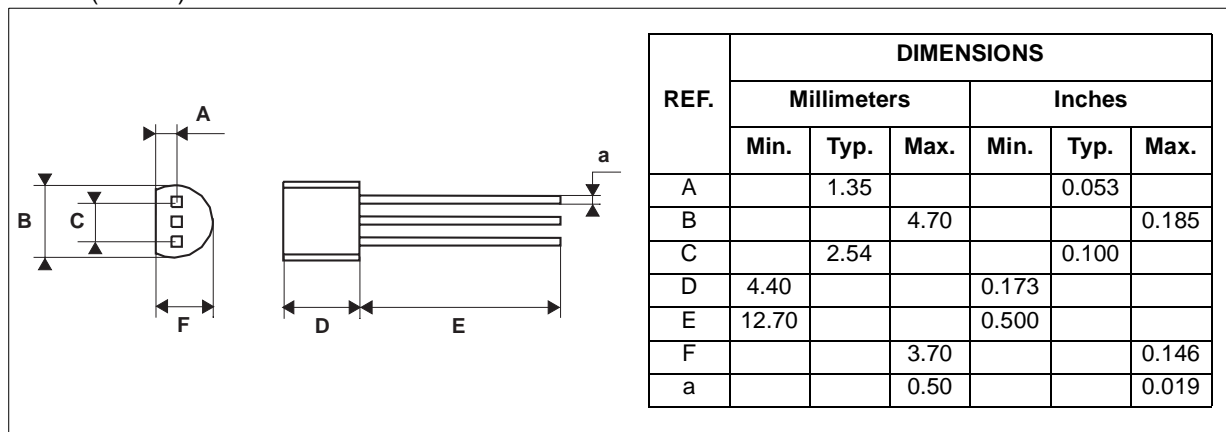


**Fig. 10:** On-state characteristics (maximum values).



## PACKAGE MECHANICAL DATA

TO-92 (Plastic)



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